Abstracts

Extension of Existing Models to MESFET's with Arbitrary Doping Density Profiles

P. de Santis. "Extension of Existing Models to MESFET's with Arbitrary Doping Density Profiles." 1979 MTT-S International Microwave Symposium Digest 79.1 (1979 [MWSYM]): 408-410.

This work extends uniform MESFET's analyses to arbitrary doping density profiles. Analytical expressions and numerical computations are provided for equivalent circuit elements of MESFET's with gaussian, exponential, inverse cubic, and "power series" profiles. A good agreement with experiment is found for ion implanted devices.

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